

SABC back-contact cell technology

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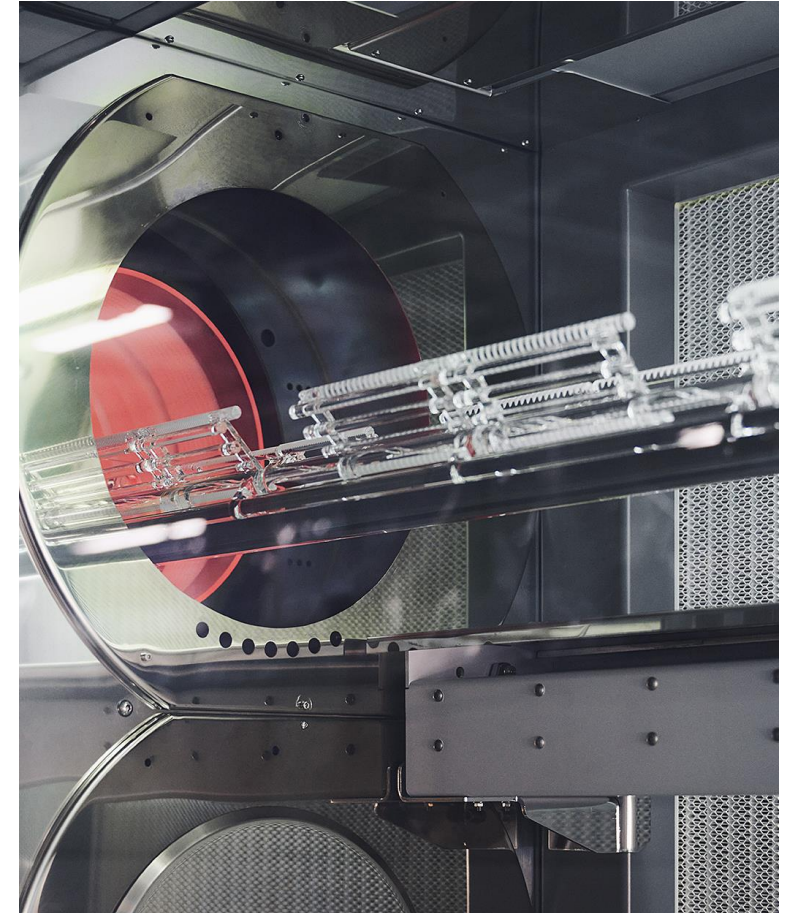
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EnPV: founded by a utility company consistently focusing on renewables

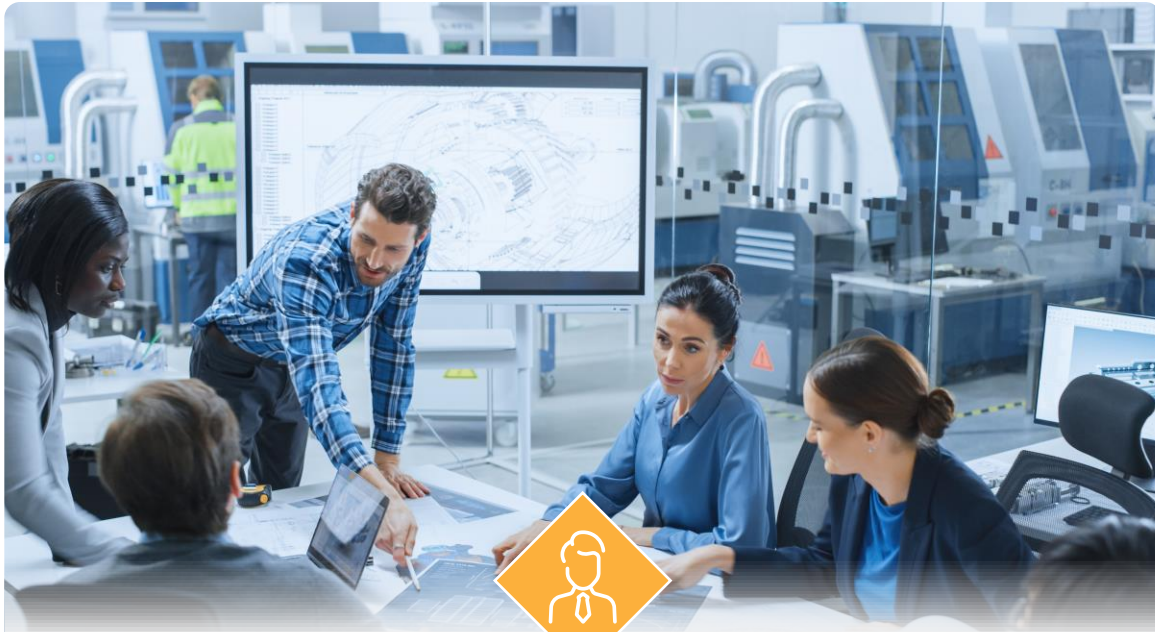


- ◆ EnPV GmbH is a subsidiary of [EnBW Energie Baden-Württemberg AG](#), a leading European utility company.
- ◆ Based in Germany, EnBW puts a strong focus on renewable energy in Europe, currently operating 3.5 GW_p wind and solar parks – with 22 GW_p in the pipeline.
- ◆ EnPV is part of EnBW's research portfolio. EnPV is focused on next-generation PV-technology:
 - in Sep 2017 EnBW started a project in collaboration with University of Stuttgart to develop a cost-effective IBC cell;
 - at the end of 2017 EnBW transferred the project to EnPV GmbH, to exploit commercially the project's results;
 - in 2024 EnPV presents its proprietary technology SABC¹, a highly competitive TOPCon IBC cell architecture with significantly reduced production cost compared to TOPCon.
- ◆ **EnBW wants EnPV to industrialise its assets with an exclusive partner.**



¹ Self-Aligned Back-Contact, patent pending.

Highly motivated team of leading experts in back-contact cell technology



International team with 75+ years of accumulated experience in solar cell device and production technology

- Development of SABC is driven by a dedicated team around the inventors of SABC, led by M. Centazzo
- 7 people strong team, of which 3 PhD's in physics/electrical engineering, and 4 M.Sc. in Physics/Electrical Engineering
- international team with diversified backgrounds from Europe, Asia, and the USA
- 75+ years of accumulated experience in solar cell device and production technology
- experimental work done at [ISFH](#)¹ (Hamelin, Germany) under the leadership – and with the support of – EnPV's team.

Expertise and experience in:

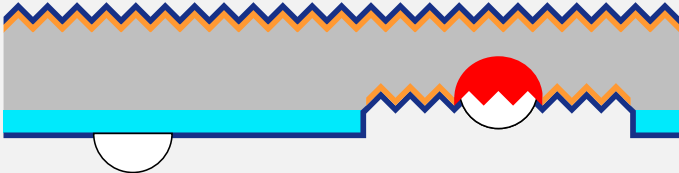
- LASER Physics and application;
- thermal processes and sputtering;
- wet-chemical processes;
- Quokka simulation;
- technology transfer into mass production;
- financial modelling of cell production;
- project management and funding acquisition.

¹ With the exception of the photo in this slide (source: Gorodenkoff, [stock.adobe.com](https://www.adobe.com/stock)), all other photos in this document were taken at ISFH, with friendly permission of the same.

Capabilities for next-gen cell technology were built up in three stages

AI BSF IBC cell (2018 – 2021)

n-type IBC cell with LASER diffused base contact



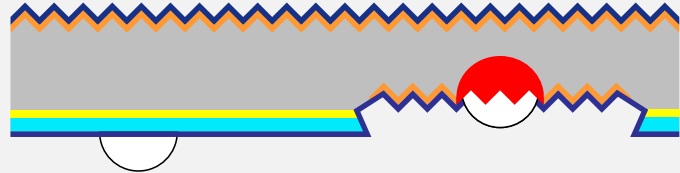
n-type Si wafer
 Front/Back Surface Field
 Base contact
 B diffused emitter
 Passivating layer
 Metallisation

**Boron diffused emitter
LASER diffused base contact**

Potential $V_{oc} = 702$ mV
 Achieved $V_{oc} = 700$ mV

HyBC (2022 – 2023)

n-type IBC cell with passivated emitter



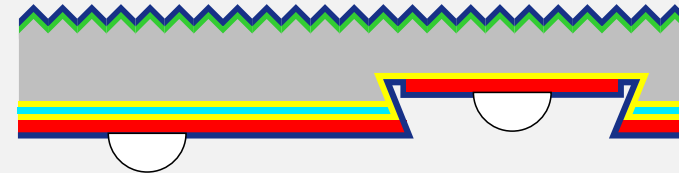
n-type Si wafer
 Front/Back Surface Field
 Tunnelling oxide
 Base contact
 p-type poly-Si
 Passivating layer
 Metallisation

***p*-type poly-Si emitter
LASER diffused base contact**

Potential $V_{oc} = 727$ mV
 Achieved $V_{oc} = 702$ mV before migrating to SABC

SABC (2024 – present)

fully passivated *n*-type IBC cell with self-aligned (trench-less) phase insulation (TLI¹)



n-type Si wafer
 Front Floating Emitter
 Tunnelling oxide
 n-type poly-Si
 p-type poly-Si
 Passivating layer
 Metallisation

***p*-type poly-Si emitter
n-type poly-Si base contact**

Potential $V_{oc} = 740$ mV
 Status 08/2024 $V_{oc} = 708$ mV

¹ Trench-Less Insulation™.

How to enable TOPCon IBC

Zhong Baoshen, Chairman at LONGi



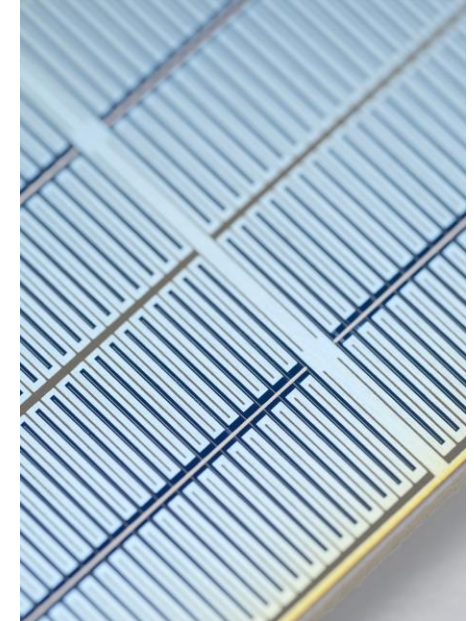
Of course, we know that efficiency and **cost are critical** factors in cell technology, but there should be a balance between the two. After exhaustive research, out of all the technologies we have explored, the objective of achieving the highest efficiency has ultimately led us to BC cells. Whether it's IBC, our own HPBC, HBC as an evolution of HIT or TBC, you can see that all these technologies ultimately lead to the BC structure. That said, **the BC structure has historically been complex in terms of the manufacturing process** and also high in cost terms, which has proven a fundamental obstacle to BC cell development.



How does SABC remove these complexities?

SABC exploits self-alignment. Hence:

- SABC removes the complexity
- SABC takes care of the cost challenge



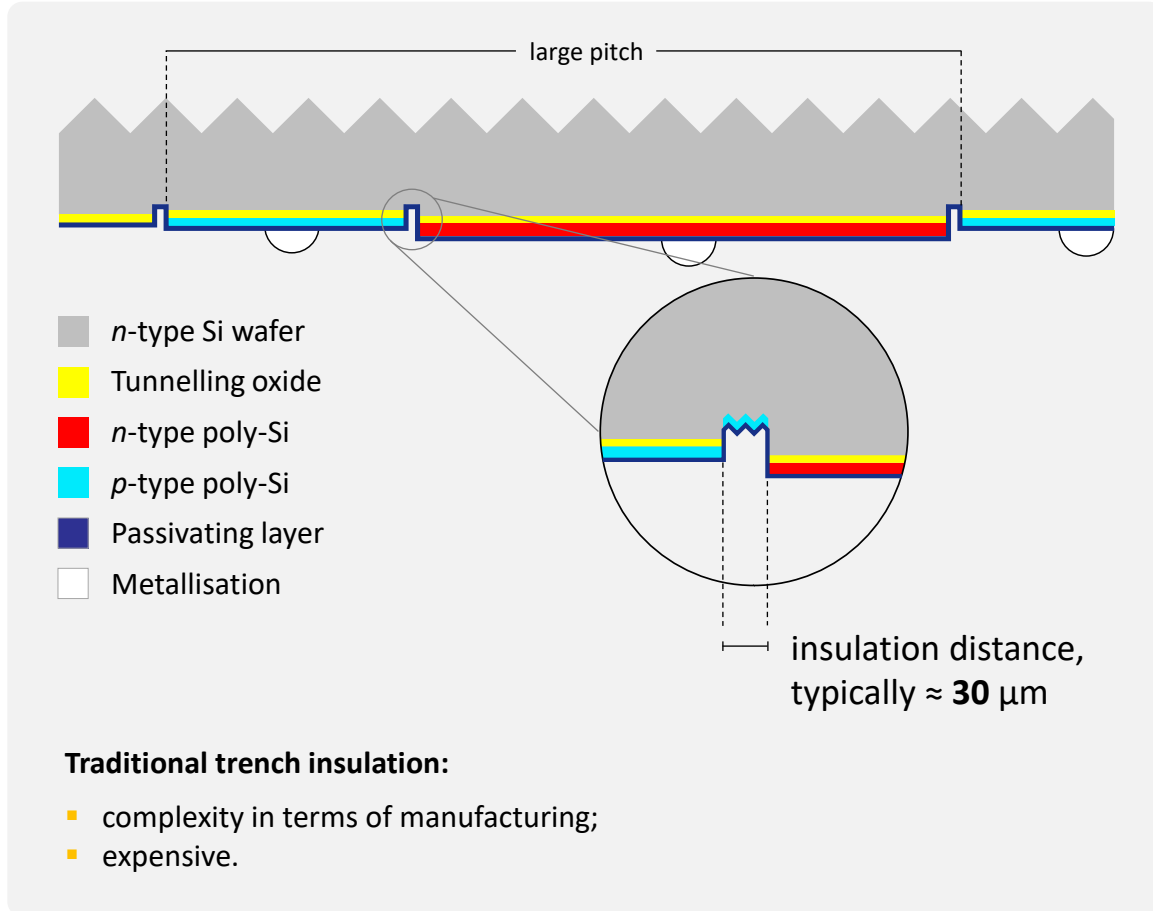
SABC's wafer-to-cell conversion cost are 15% lower than TOPCon's

¹ Source: PV-TECH.ORG.

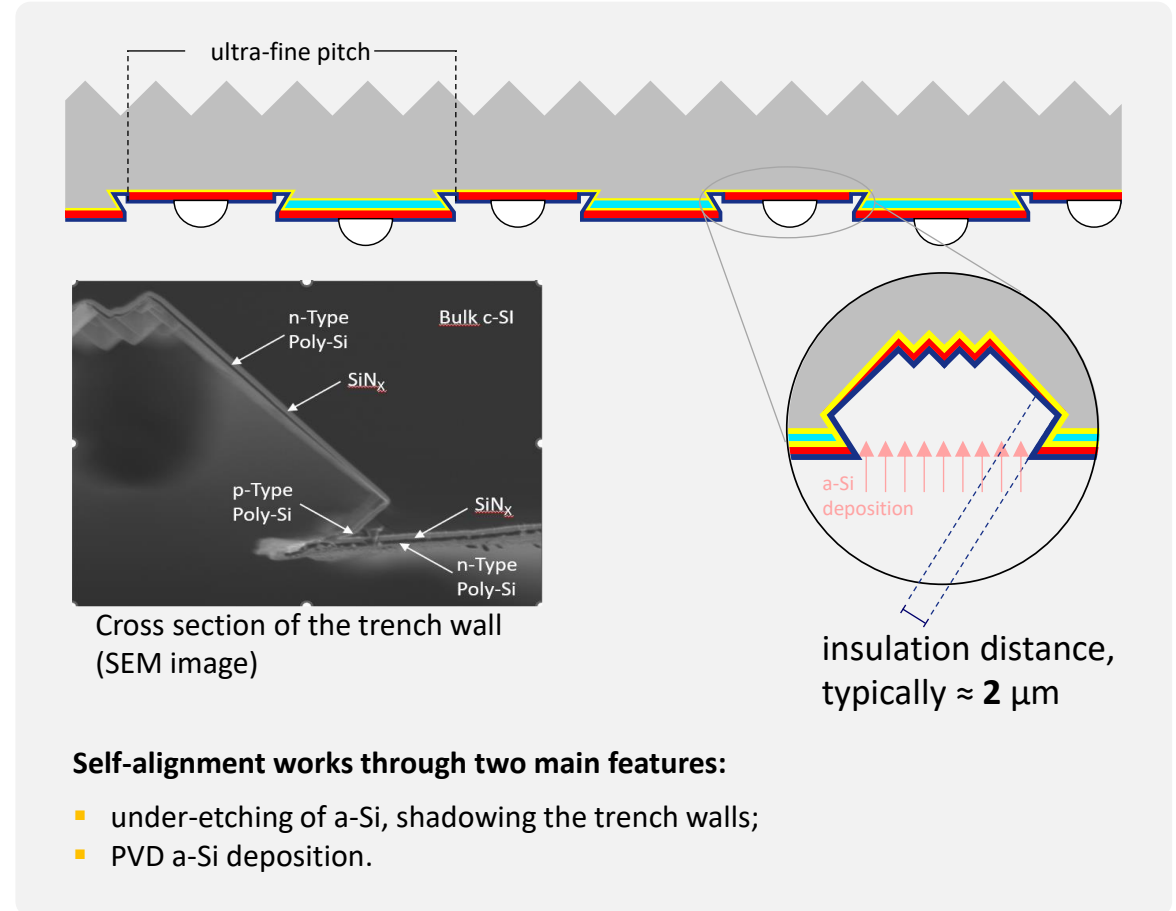
Conquering complexity I

Self-aligned phase insulation on IBC back-side

Typical IBC insulation
(simplified sketch)



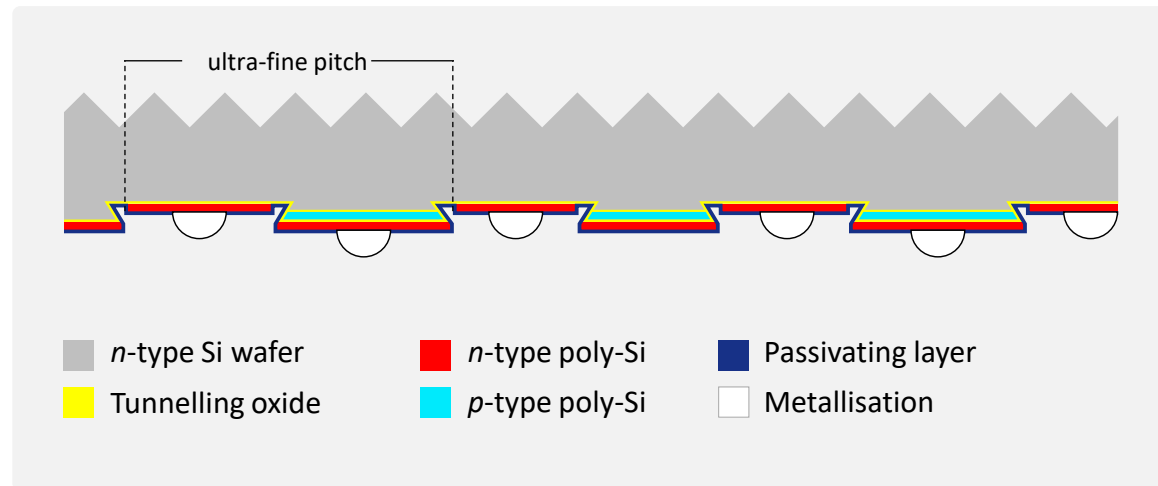
SABC self-aligned insulation, TLI
(simplified sketch)



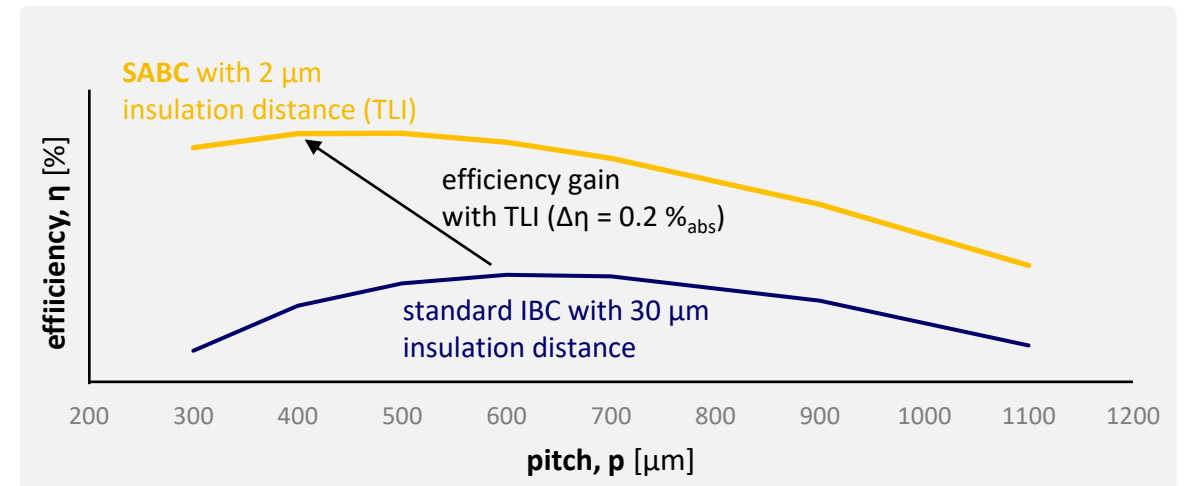
Conquering complexity II

Laser structuring combined with TLI enables ultra-fine pitch and very small insulation distance

SABC's ultra-fine pitch of 400 μm (simplified sketch)



Reducing insulation distance from 30 μm to 2 μm leads to 0,2%_{abs} more efficiency



On-the-fly laser structuring (ultra-fine pitch) technology:

- 526 lines for M12 wafer;
- 451 lines for M10 wafer;
- 0,6 J/cm² energy density;
- 150 m/sec (> 500 km/h) laser spot speed;
- 2 sec per wafer scan time;
- $\pm 8 \mu\text{m}$ (3σ) scanned line-pattern congruence to drawing.

On-the-fly laser structuring (ultra-fine pitch) advantages:

- reliable;
- high efficiency through small pitch;
- cost effective;
- virtually no environmental impact.

Easy upgrade TOPCon to SABC thanks to only two additional tools

SABC manufacturing sequence: adding two tools¹

Pos Measure/Equipment

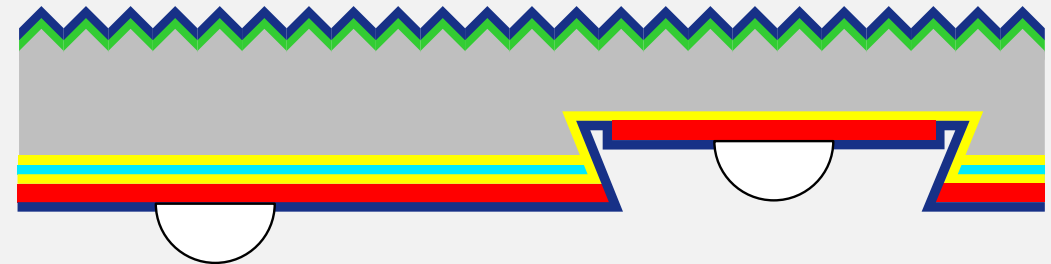
1	alkaline texture
2	BCl ₃ diffusion
3	BSG etch + SDE rear + 1 st tunneling oxide
4	<i>p</i> -poly deposition etch barrier deposition
5	LASER structuring
6	SDE + BSG + barrier etch rear + 2 nd tunneling oxide
7	<i>n</i> -poly deposition
8	<i>n</i> / <i>p</i> -poly annealing + oxidation
9	cleaning
10	front side SiN _x
11	rear side SiN _x
12	back-end

SDE = Saw-Damage Etch

Additional equipment

BSG = BoroSilicate Glass

Recipe adjustments when upgrading from TOPCon¹ to SABC:

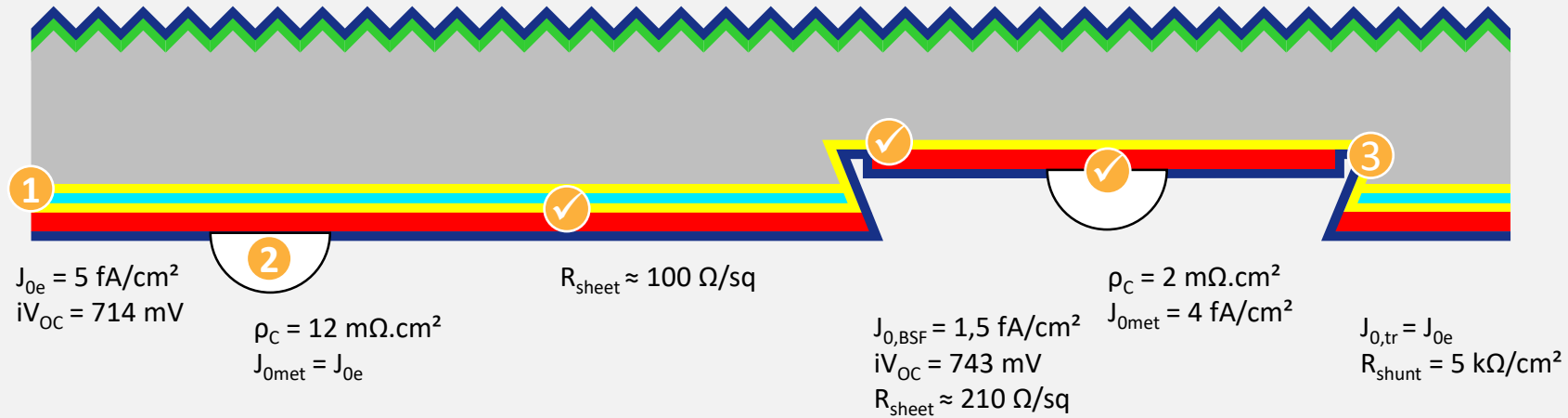


- n*-type Si wafer
- Front Floating Emitter
- Tunnelling oxide
- n*-type poly-Si
- p*-type poly-Si
- Passivating layer
- Metallisation

- convert *n*-poly deposition (step 4) to *p*-poly deposition, add etch barrier deposition (SiN_x)
- add LASER structuring and PVD deposition of *n*-poly
- change recipes, in particular for second wet bench (step 6)
- metallisation needs two printing steps (Ag and Cu) only, sequence would change (Ag print, fast-firing, Cu-print, curing)
- chuck in cell tester is replaced by back-contact chuck
- train personnel on additional equipment

¹ Depending on TOPCon line specification.

Key steps towards top efficiency have been made ...



✓ Features at target-level

n Features needing further optimisation in lab and pilot line:

- 1 optimisation of *n*-poly Si quality
- 2 metallisation
- 3 *n/p* phase separation

■ *n*-type Si wafer

■ Front Floating Emitter

■ Tunnelling oxide

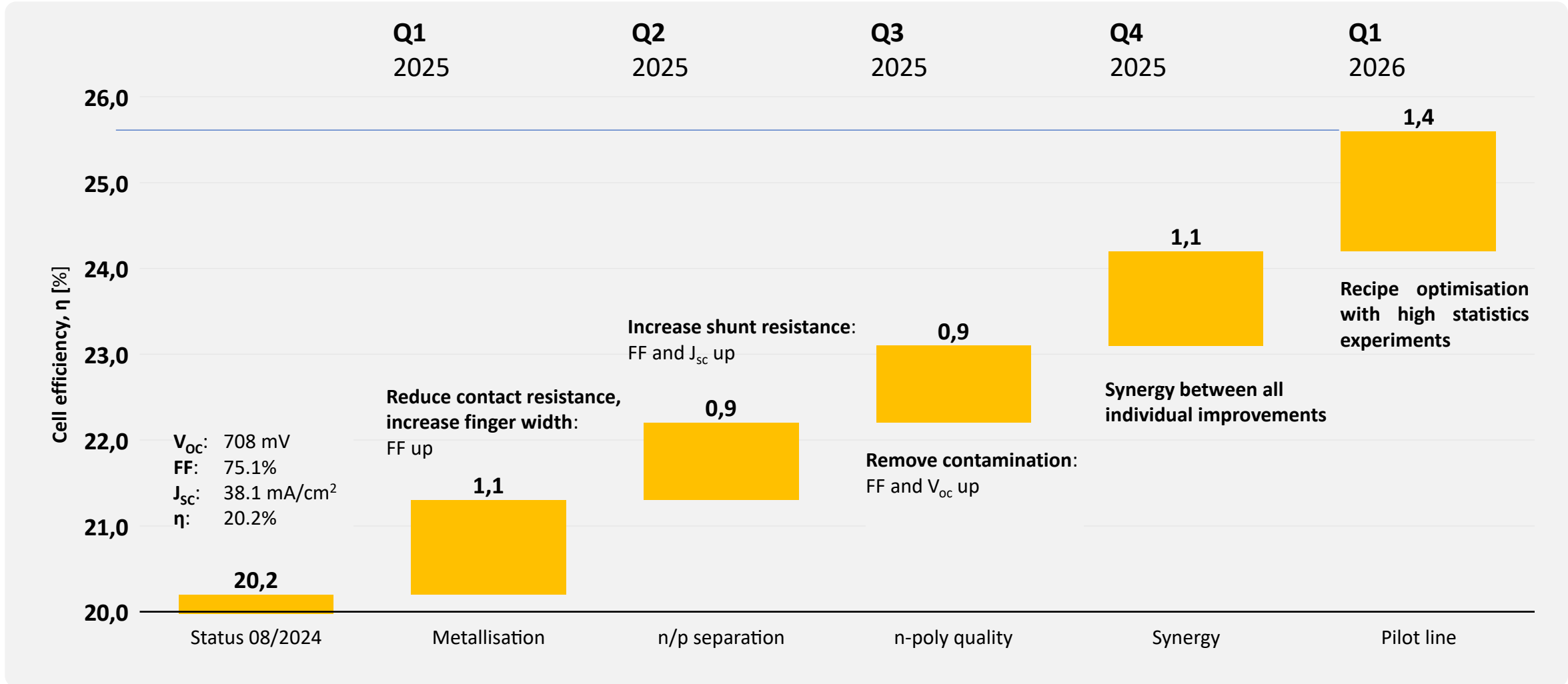
■ *n*-type poly-Si

■ *p*-type poly-Si

■ Passivating layer

■ Metallisation

... and a clear plan has been devised



Technology readiness level TRL6 is achieved

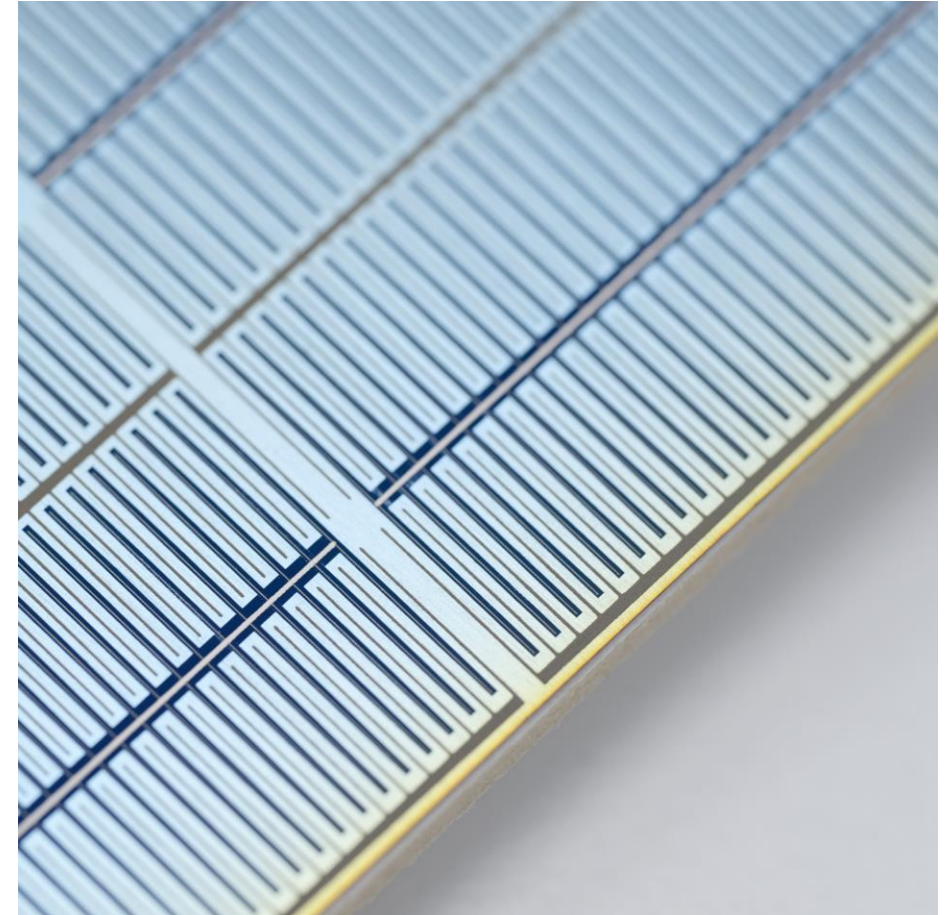
- ◆ SABC's underlying technology concepts are proven
- ◆ all process steps can be demonstrated on industrial mass-production equipment
- ◆ prototype cells can be produced in small quantities¹
- ◆ the efficiency potential ($> 0,5\%_{\text{abs}}$ higher than the best TOPCon cell performance) is proven in Quokka simulations fed with trustworthy data known from TOPCon production and experiments of EnPV's
- ◆ an exemplary production line including equipment has been specified. Due to the proximity to TOPCon production the equipment specification is highly reliable. The additional equipment (LASER and PVD, to be added to upgrade TOPCon to SABC) is extensively tested in the suppliers' laboratories



¹ With Ag-only metallisation.

Riding the wave: SABC is ready for the up turn-cum-technology change

- ◆ EnPV GmbH developed SABC¹, a novel proprietary back-contact cell (IBC) technology
- ◆ SABC dramatically simplifies all IBC fabrication methods existing to-date by the reduction of typical number of productions steps resulting in greater production efficiency
 - **SABC decreases wafer-to-cell conversion cost by > 15% compared to TOPCon.**
- ◆ Essential parts of SABC (TLI²) are protected IP
- ◆ **EnPV is looking for an exclusive partnership to implement SABC into a pilot production.**



¹ Self-Aligned Back Contact.

² Trench-Less Insulation.

Contact



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